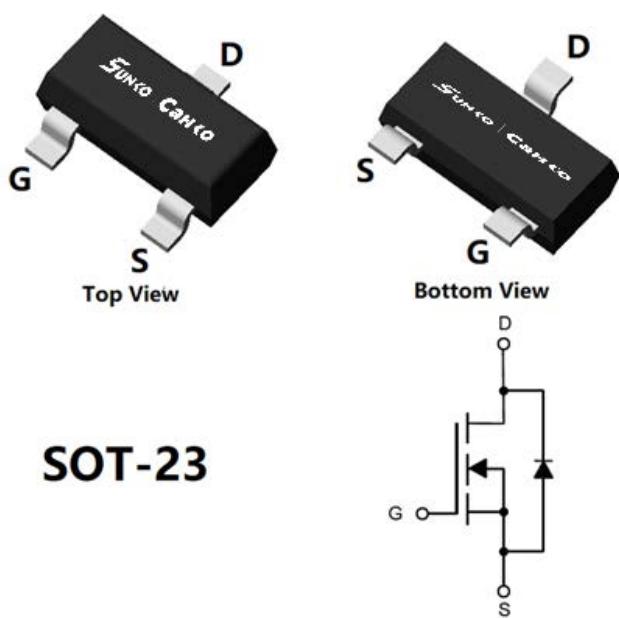


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} 20V
- I_D 3.0A
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <50 mohm
- $R_{DS(ON)}$ (at $V_{GS}=2.5V$) <70 mohm

General Description

- Trench Power LV MOSFET technology
- High Power and current handing capability
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- PWM application
- Load switch

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	20	V
Gate-source Voltage		V_{GS}	± 10	V
Drain Current	$T_A=25^\circ\text{C}$ @ Steady State	I_D	3.0	A
	$T_A=70^\circ\text{C}$ @ Steady State		2.4	
Pulsed Drain Current ^A		I_{DM}	14	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$		P_D	0.7	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B		$R_{\theta JA}$	178	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCL2302B	F2	2302B.	3000	30000	120000	7" reel

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	20			V
Zero Gate Voltage Drain Current	$I_{\text{DS}0}$	$V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}, T_c=25^\circ\text{C}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}= \pm 10\text{V}, V_{\text{DS}}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}= V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.55	0.78	1.1	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}= 4.5\text{V}, I_{\text{D}}=3.0\text{A}$		38.5	50	$\text{m}\Omega$
		$V_{\text{GS}}= 2.5\text{V}, I_{\text{D}}=2.0\text{A}$		53.5	70	
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=3.0\text{A}, V_{\text{GS}}=0\text{V}$			1.2	V
Maximum Body-Diode Continuous Current	I_{S}				3.0	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=10\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		220		pF
Output Capacitance	C_{oss}			34		
Reverse Transfer Capacitance	C_{rss}			26		
Switching Parameters						
Total Gate Charge	Q_g	$V_{\text{GS}}=4.5\text{V}, V_{\text{DS}}=10\text{V}, I_{\text{D}}=3.0\text{A}$		3.61		nC
Gate Source Charge	Q_{gs}			0.88		
Gate Drain Charge	Q_{gd}			0.77		
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GS}}=4.5\text{V}, V_{\text{DD}}=10\text{V}, R_{\text{L}}=1.5\Omega, R_{\text{GEN}}=3\Omega$		6.8		ns
Turn-on Rise Time	t_r			57		
Turn-off Delay Time	$t_{\text{D(off)}}$			14		
Turn-off Fall Time	t_f			53		

A. Pulse Test: Pulse Width $\leq 300\text{us}$, Duty cycle $\leq 2\%$.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

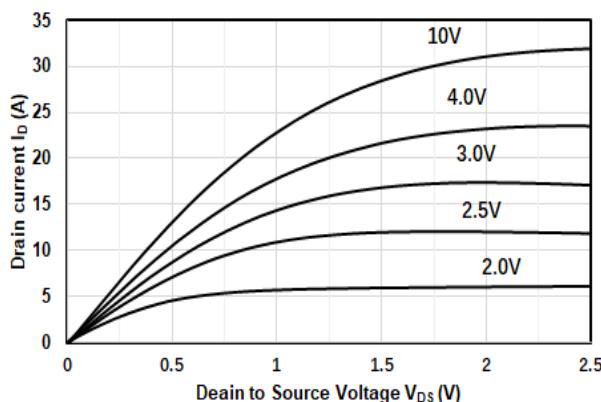


Figure1. Output Characteristics

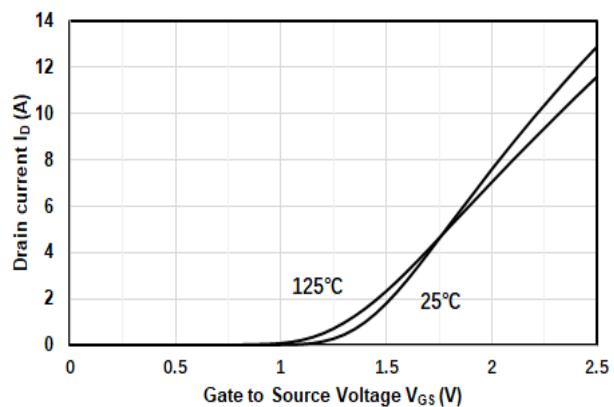


Figure2. Transfer Characteristics

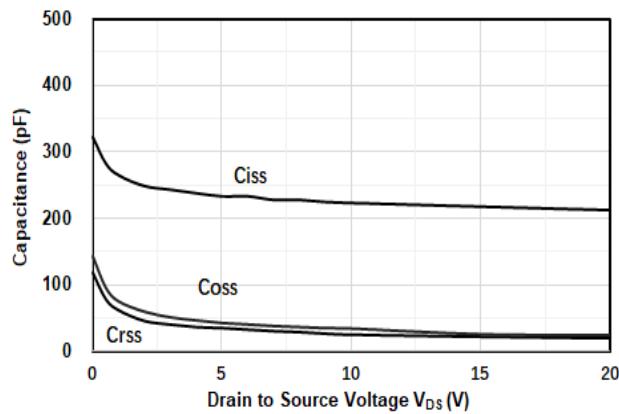


Figure3. Capacitance Characteristics

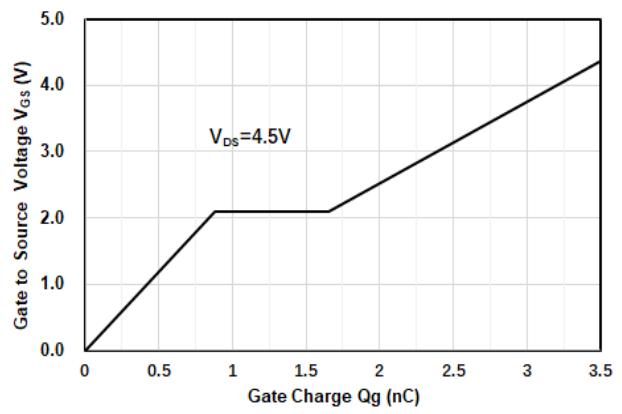


Figure4. Gate Charge

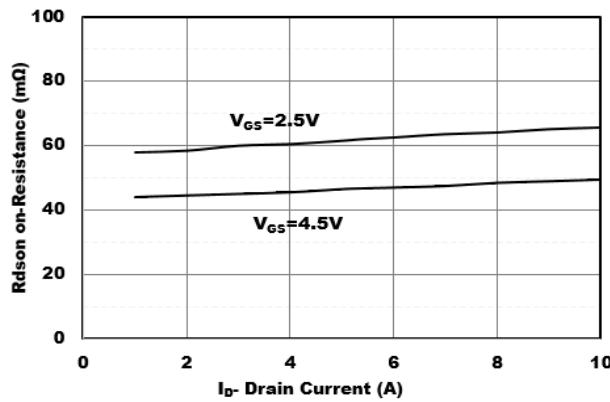


Figure5. Drain-Source on Resistance

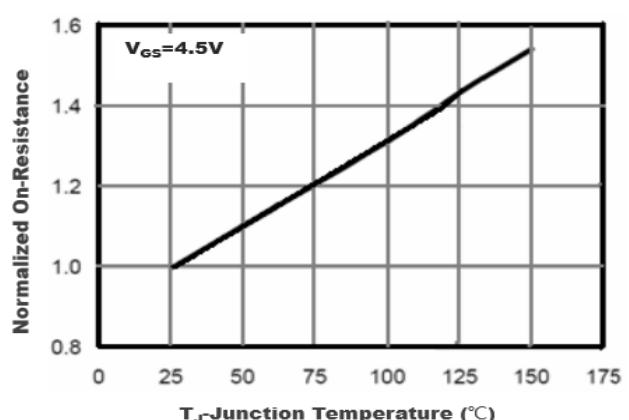


Figure6. Drain-Source on Resistance

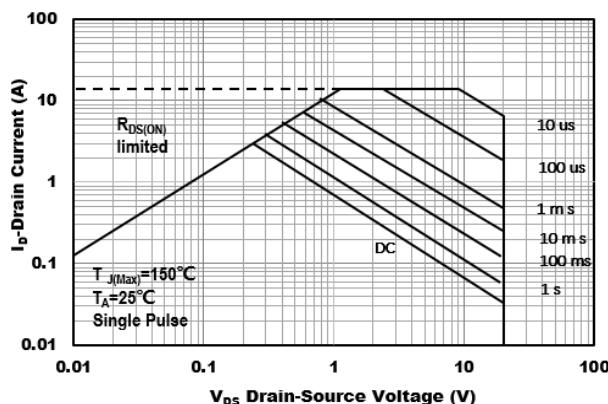


Figure 7. Safe Operation Area

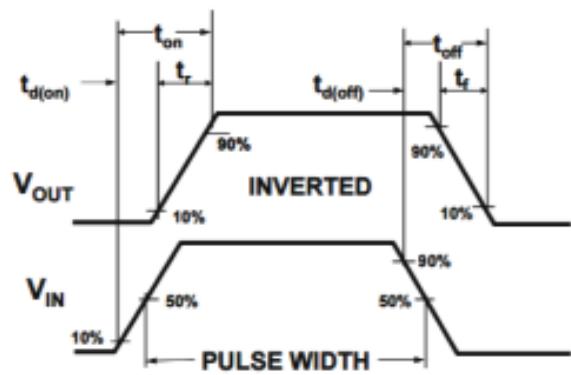


Figure 8. Switching wave

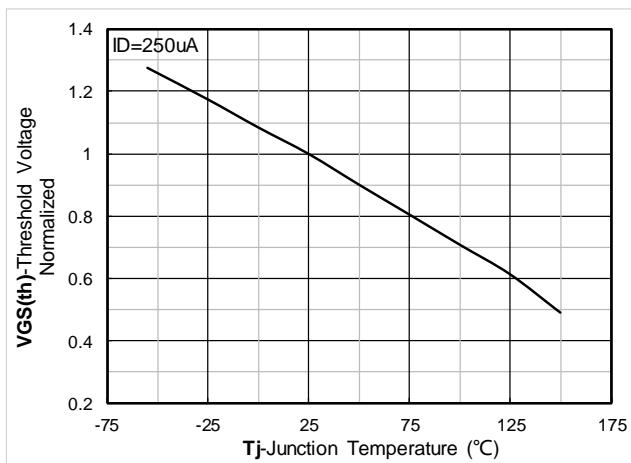


Figure 9. Normalized Threshold voltage

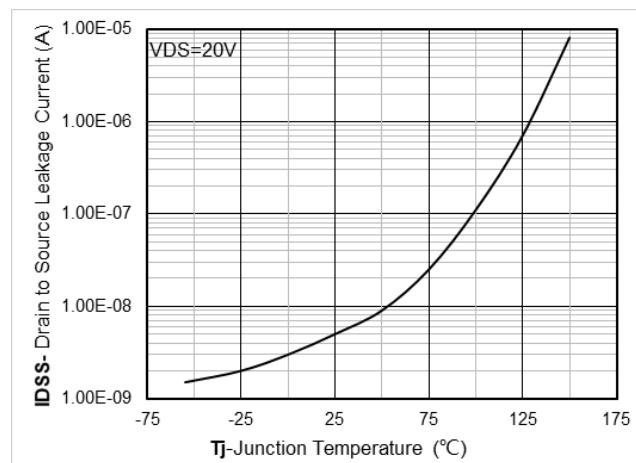
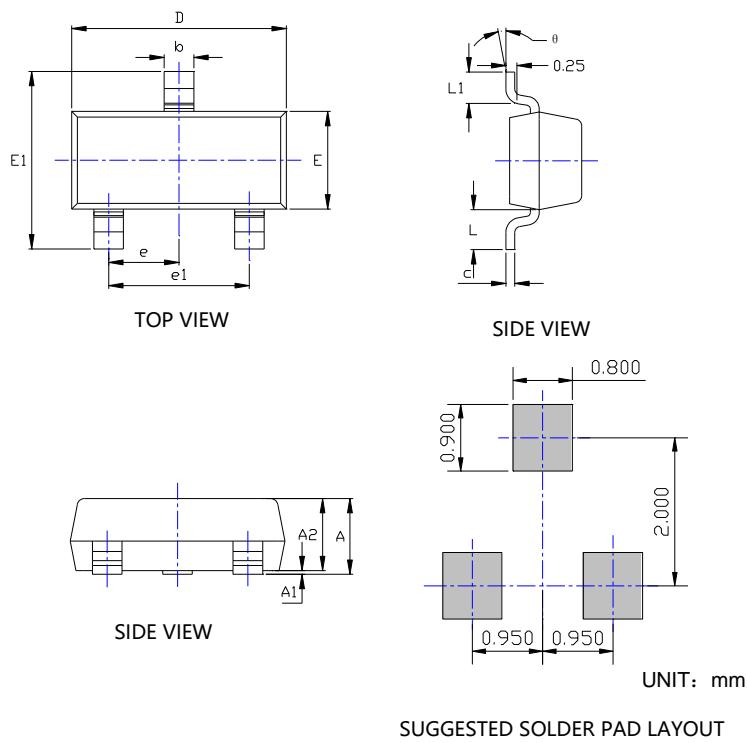


Figure 10. Drain to Source Leakage Current

■ SOT-23 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.045	0.900	1.150
A1	0.000	0.004	0.000	0.100
A2	0.035	0.041	0.900	1.050
b	0.012	0.020	0.300	0.500
c	0.004	0.008	0.100	0.200
D	0.110	0.118	2.800	3.000
E	0.047	0.055	1.200	1.400
E1	0.089	0.100	2.250	2.550
e	0.037TYP		0.950TYP	
e1	0.071	0.079	1.800	2.000
L	0.022REF		0.550REF	
L1	0.012	0.020	0.300	0.500
θ	0°	8°	0°	8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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